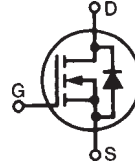


**Trench™
Power MOSFET**

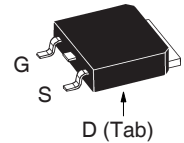
**IXTY44N10T
IXTP44N10T**

V_{DSS} = 100V
I_{D25} = 44A
R_{DS(on)} ≤ 30mΩ

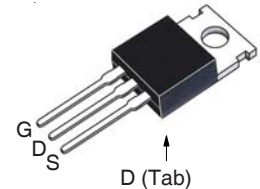
N-Channel Enhancement Mode
Avalanche Rated



**TO-252
(IXTY)**



**TO-220
(IXTP)**



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V _{DSS}	T _J = 25°C to 175°C	100	V
V _{DGR}	T _J = 25°C to 175°C, R _{GS} = 1MΩ	100	V
V _{GSS}	Continuous	±20	V
V _{GSM}	Transient	±30	V
I _{D25}	T _C = 25°C	44	A
I _{LRMS}	Lead Current Limit, (RMS) (TO-252)	25	A
I _{DM}	T _C = 25°C, Pulse Width Limited by T _{JM}	110	A
I _A	T _C = 25°C	10	A
E _{AS}	T _C = 25°C	250	mJ
dv/dt	I _S ≤ I _{DM} , V _{DD} ≤ V _{DSS} , T _J ≤ 175°C	12	V/ns
P _D	T _C = 25°C	130	W
T _J		-55 ... +175	°C
T _{JM}		175	°C
T _{stg}		-55 ... +175	°C
T _L	Maximum Lead Temperature for Soldering	300	°C
T _{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
M _d	Mounting Torque (TO-220)	1.13 / 10	Nm/lb.in.
Weight	TO-252	0.35	g
	TO-220	3.00	g

Features

- International Standard Packages
- 175°C Operating Temperature
- Avalanche Rated
- Low R_{DS(on)}
- High Current Handling Capability

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- Automotive
 - Motor Drives
 - 24 / 48V Power Bus
 - ABS Systems
- DC/DC Converters and Off-Line UPS
- Primary- Side Switch
- High Current Switching Applications

Symbol	Test Conditions (T _J = 25°C Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV _{DSS}	V _{GS} = 0V, I _D = 250μA	100		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 25μA	2.5		4.5 V
I _{GSS}	V _{GS} = ± 20V, V _{DS} = 0V			±100 nA
I _{DSS}	V _{DS} = V _{DSS} , V _{GS} = 0V T _J = 150°C			1 μA
				200 μA
R _{DS(on)}	V _{GS} = 10V, I _D = 0.5 • I _{D25} , Notes 1, 2			30 mΩ

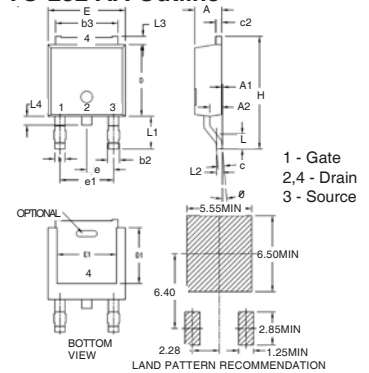
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}$, $I_D = 0.5 \cdot I_{D25}$, Note 1	13	21	S
C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$		1567	pF
C_{oss}			200	pF
C_{rss}			47	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 10\text{A}$ $R_G = 18\Omega$ (External)		21	ns
t_r			47	ns
$t_{d(off)}$			36	ns
t_f			32	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 0.5 \cdot V_{DSS}$, $I_D = 0.5 \cdot I_{D25}$		27.4	nC
Q_{gs}			8.8	nC
Q_{gd}			9.0	nC
R_{thJC}	TO-220		0.50	1.15 $^\circ\text{C/W}$
R_{thCH}				$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			44 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			140 A
V_{SD}	$I_F = 22\text{A}$, $V_{GS} = 0\text{V}$, Note 1			1.1 V
t_{rr}	$I_F = 0.5 \cdot I_{D25}$, $V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 50\text{V}$		60	ns
I_{RM}			4.8	A
Q_{RM}			144	nC

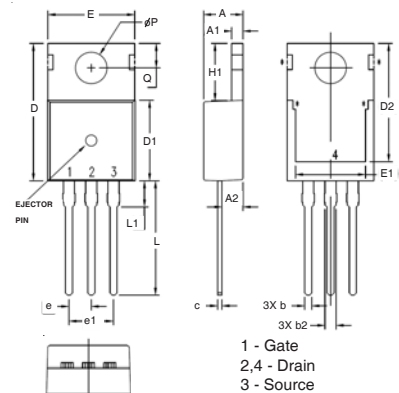
- Notes: 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. On through-hole packages, $R_{DS(on)}$ Kelvin test contact location must be 5mm or less from the package body.

TO-252 AA Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.086	.094	2.19	2.38
A1	0	.005	0	0.12
A2	.038	.046	0.97	1.17
b	.025	.035	0.64	0.89
b2	.030	.045	0.76	1.14
b3	.200	.215	5.08	5.46
c	.018	.024	0.46	0.61
c2	.018	.023	0.46	0.58
D	.235	.245	5.97	6.22
D1	.180	.205	4.57	5.21
D2	.250	.265	6.35	6.73
E	.170	.205	4.32	5.21
e	.090 BSC		2.28 BSC	
e1	.180 BSC		4.57 BSC	
H	.370	.410	9.40	10.42
L	.055	.070	1.40	1.78
L1	.100	.115	2.54	2.92
L2	.020 BSC		0.50 BSC	
L3	.025	.040	0.64	1.02
L4	.025	.040	0.64	1.02
theta	0*	10*	0*	10*

TO-220 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.169	.185	4.30	4.70
A1	.047	.055	1.20	1.40
A2	.079	.106	2.00	2.70
b	.024	.039	0.60	1.00
b2	.045	.057	1.15	1.45
c	.014	.026	0.35	0.65
D	.587	.626	14.90	15.90
D1	.335	.370	8.50	9.40
(D2)	.500	.531	12.70	13.50
E	.382	.406	9.70	10.30
(E1)	.283	.323	7.20	8.20
e	.100 BSC		2.54 BSC	
e1	.200 BSC		5.08 BSC	
H1	.244	.268	6.20	6.80
L	.492	.547	12.50	13.90
L1	.110	.154	2.80	3.90
theta	.134	.150	3.40	3.80
Q	.106	.126	2.70	3.20

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

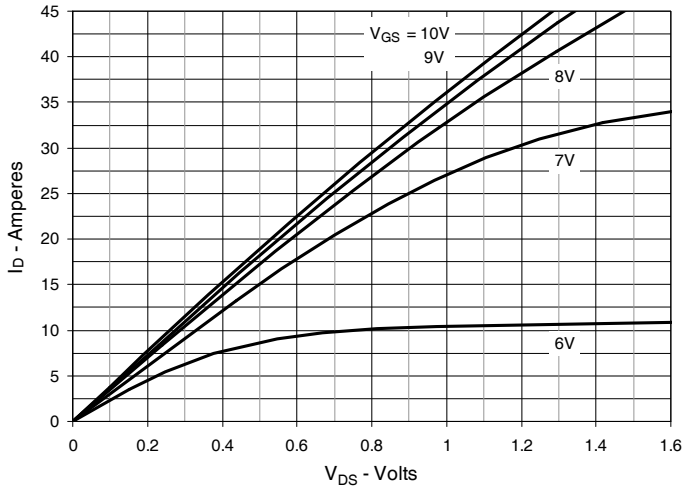


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

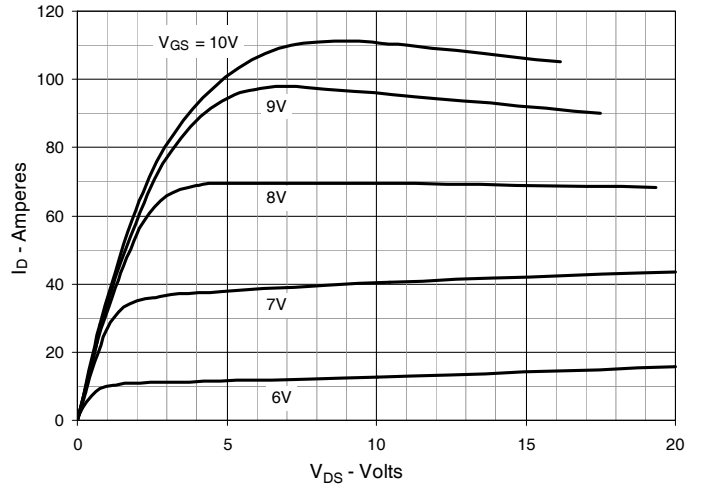


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

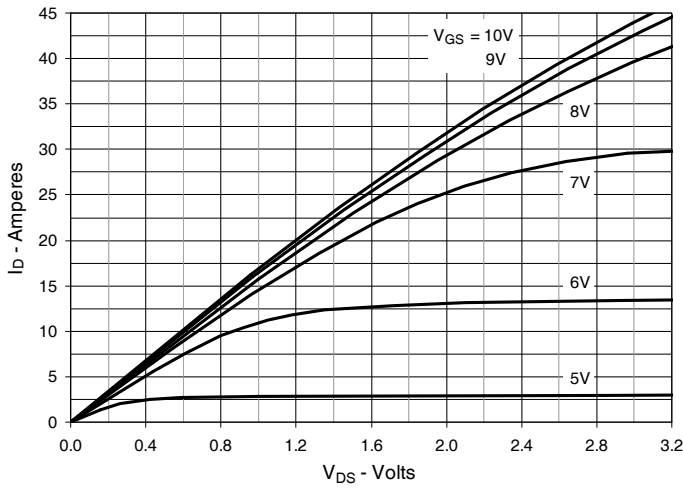


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 22\text{A}$ Value vs. Junction Temperature

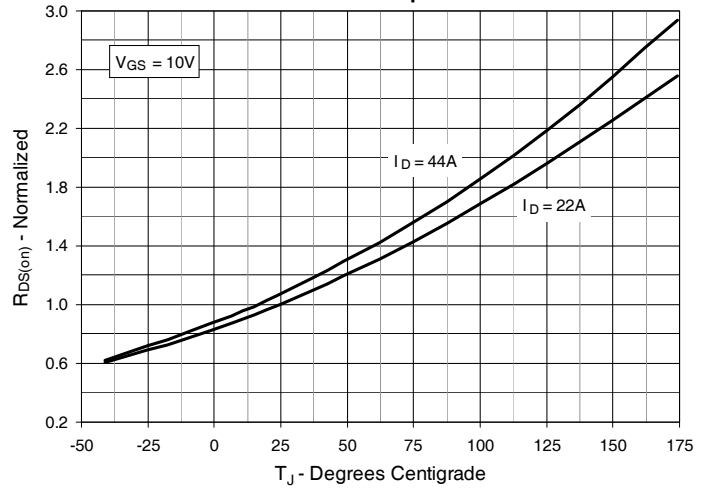


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 22\text{A}$ Value vs. Drain Current

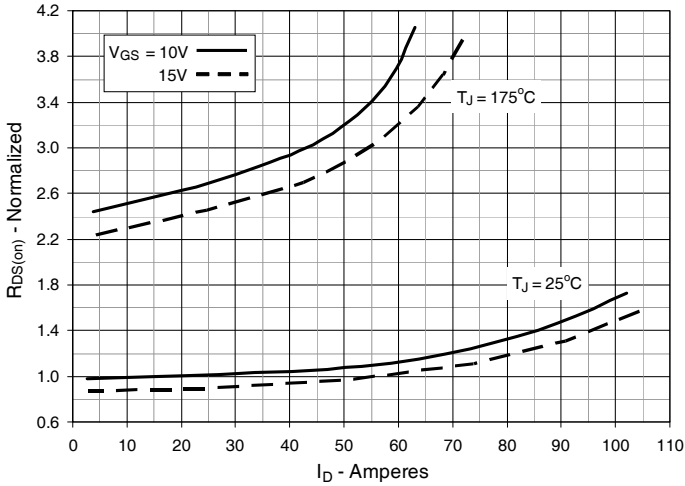


Fig. 6. Drain Current vs. Case Temperature

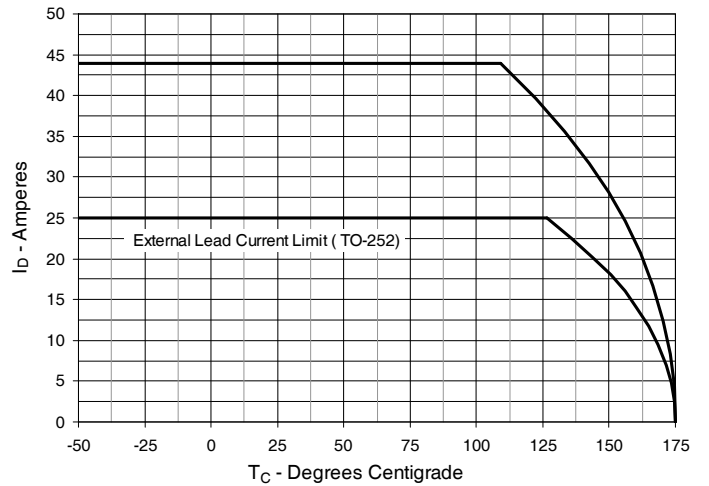


Fig. 7. Input Admittance

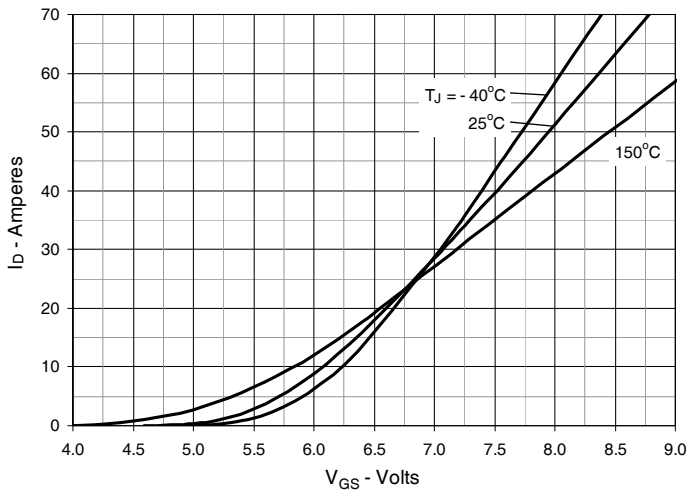


Fig. 8. Transconductance

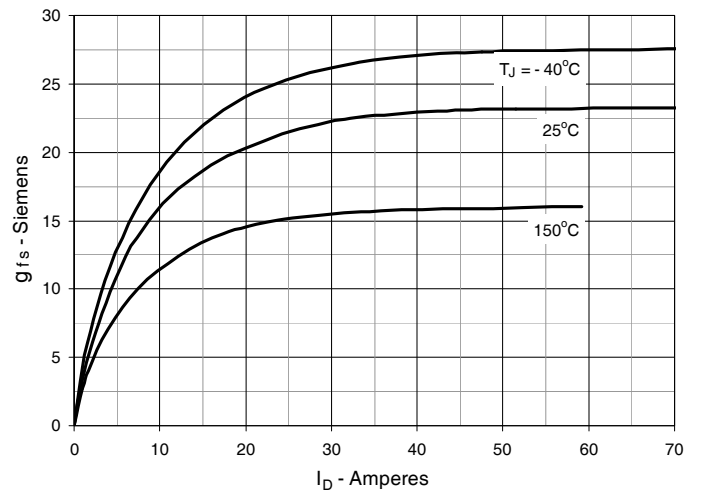


Fig. 9. Forward Voltage Drop of Intrinsic Diode

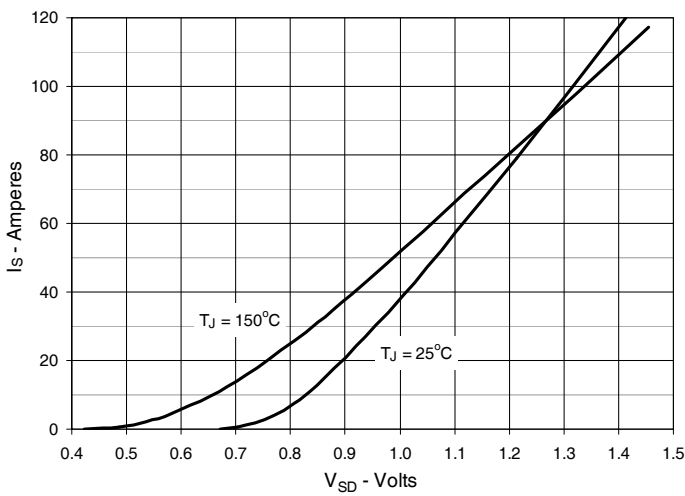


Fig. 10. Gate Charge

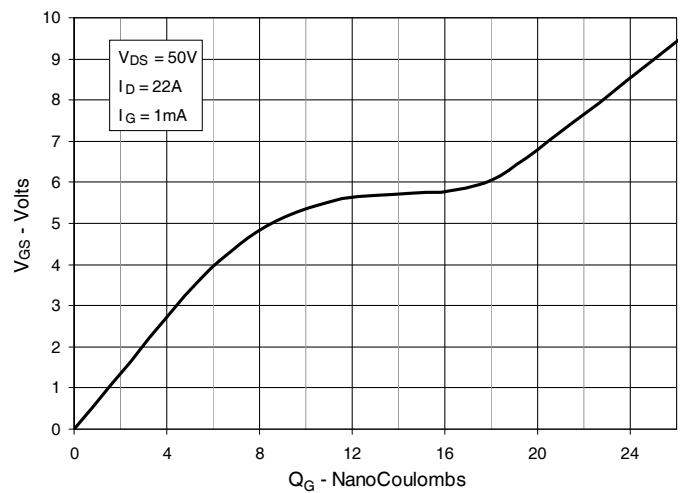


Fig. 11. Capacitance

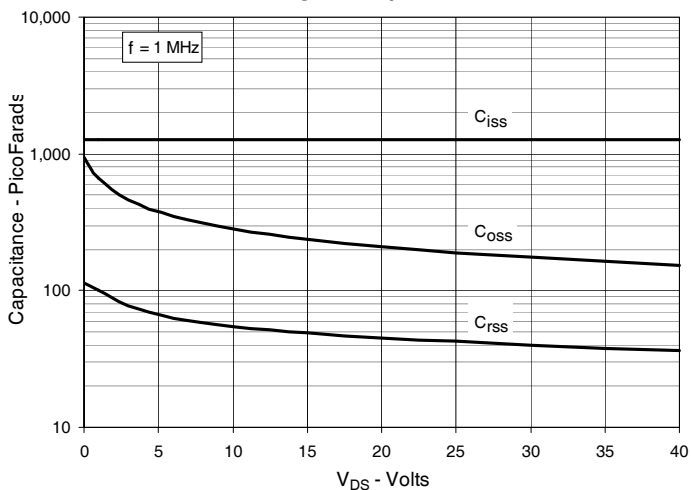


Fig. 12. Forward-Bias Safe Operating Area

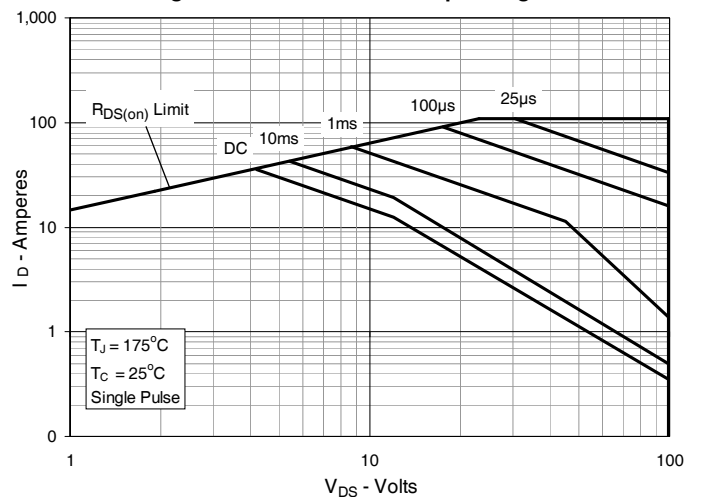


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

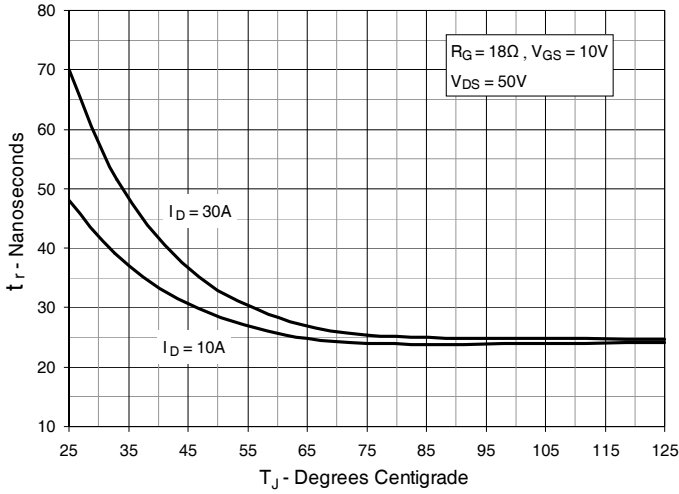


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

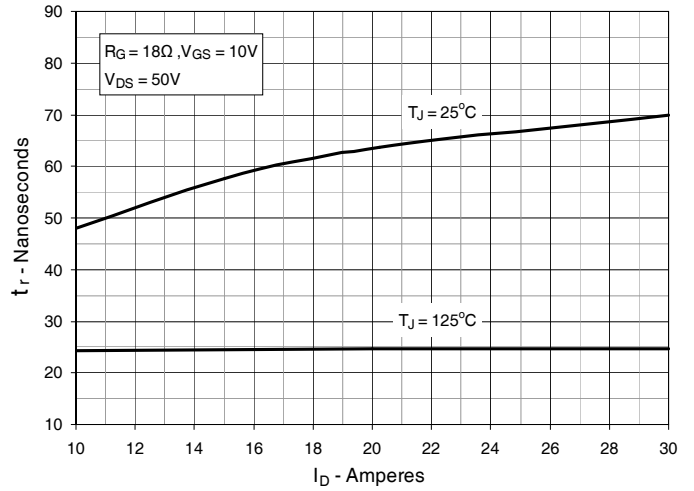


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

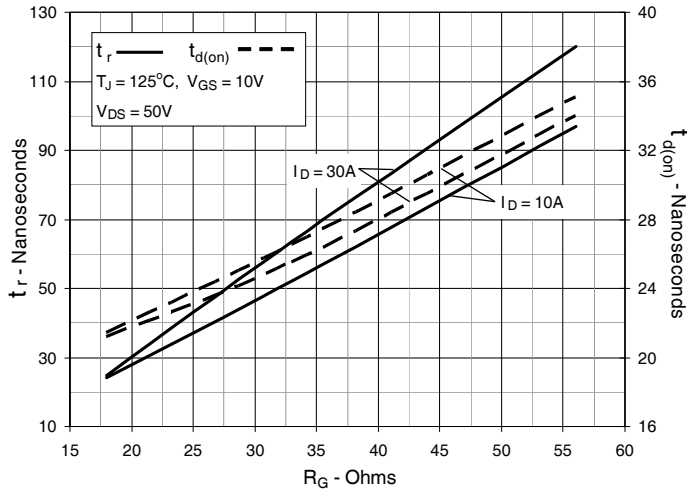


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

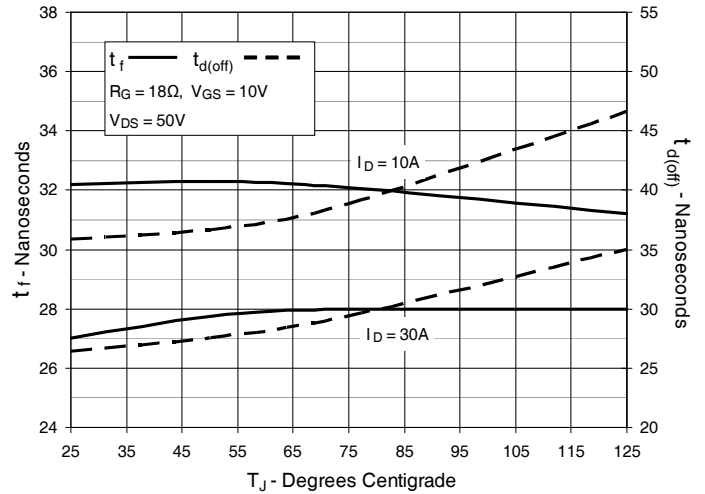


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

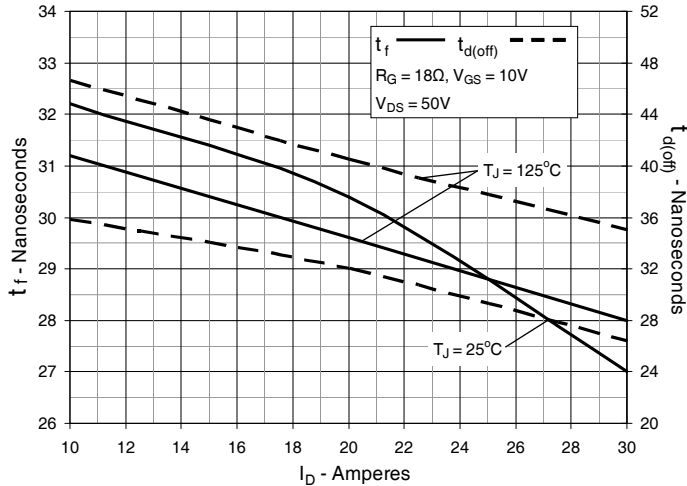


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

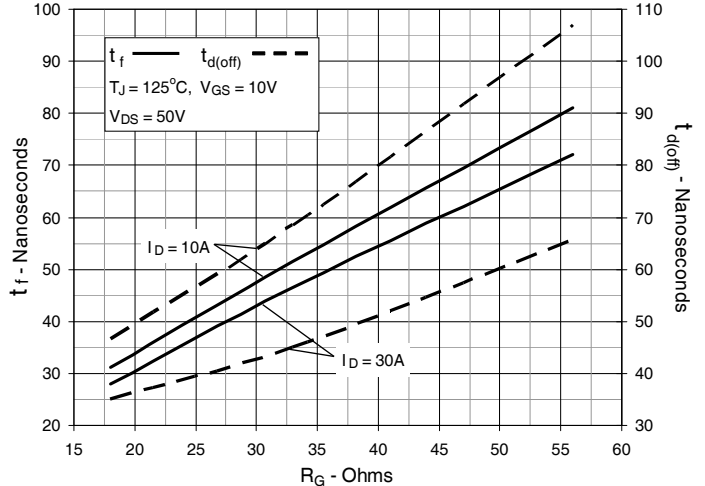


Fig. 19. Maximum Transient Thermal Impedance

